

NEWS RELEASE



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FOR IMMEDIATE RELEASE

Peregrine Semiconductor Unveils PE42110 MultiSwitch™ Flip Chip RFIC

Next-generation handset complexity demands sophisticated front-end switch function

San Diego, California, June 5, 2007 -- Peregrine Semiconductor Corporation, a leading supplier of high-performance RF CMOS and mixed-signal communications ICs, today unveiled the UltraCMOS™ PE42110 multiple switch IC for advanced multi-band WCDMA handsets. Labeled the "MultiSwitch™" RFIC, the device incorporates four independent high performance RF switch devices on a monolithic flip-chip IC controlled by a single onboard CMOS controller providing for more than 85% size reduction over alternate solutions.

Next-generation handsets now being developed incorporate tri-band WCDMA and quad-band EDGE platforms, an architecture which demands seven radios in a single handset. This has greatly complicated the RF front-end by more than tripling the high power signal paths engineered in today's quad-band EDGE handsets. Because switching signals to and from a duplexer and filter banks are utilized in these next-generation designs, the burden to the switching function becomes high. The new applications require: very low insertion loss due to the signal going through two switch paths; very high linearity due to its WCDMA platform; an effective switch solution for 4 independent, simultaneous signal paths and up to 14 control states; and very high isolation of >+55 dB for critical paths. Peregrine's UltraCMOS technology enabled the PE42110 to meet these specifications, making it the only device delivering an efficient solution to the combined tri-band WCDMA/quad-band EDGE RF switching requirement by demonstrating the ability to integrate multiple switching devices, onboard controllers, high reliability, ESD tolerance and exceptional RF performance.

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ADD ONE/PE42110 RF Switch

The UltraCMOS™ -based PE42110 incorporates Peregrine's revolutionary HaRP™ technology enhancements to deliver exceptional harmonic results, linearity and overall RF performance: high linearity of +71 dBm IP3 or -116 dBm IMD3; low insertion loss of 0.35 dB (typ); high isolation >70 dB at critical paths; and monolithic integration of key elements including 3 control lines operating 12 independent paths.

"The UltraCMOS PE42110 demonstrates the ability of UltraCMOS to achieve RF front-end architectures and efficiencies that cannot be accomplished with any other technology," commented Rodd Novak, vice-president of marketing and business development. "Peregrine has outdistanced itself from the competition and will continue to do so as RF front-ends demand higher levels of integration coupled with leading edge RF performance," he added.

Peregrine's 50-Ohm PE42110 2.75 V RF switch operates from 100 – 3000 MHz and provides many additional features, including 1500 V HBM ESD tolerance at all ports; on-board CMOS logic which facilitates 1.8 V or 2.75 V control; no blocking capacitors; and fast switch settling time.

About UltraCMOS™ Technology and the HaRP™ Technology Invention

UltraCMOS™ mixed-signal process technology is a proprietary, patented variation of silicon-on insulator (SOI) technology on a sapphire substrate providing with high yields and competitive costs. It combines the RF, mixed-signal, and digital capabilities of any other CMOS process, yet tolerates the high power required for high-performance wireless applications. The Company's revolutionary HaRP™ technology enables dramatic improvements in harmonic results, linearity and overall RF performance; specifications required by the 3GPP standards body for GSM/WCDMA applications which are unmatched in the industry. In particular, long-awaited accomplishments in Intermodulation Distortion (IMD) handling are now available monolithically to multi-band front-end module and handset manufacturers. These significant performance advantages exist over competing processes such as GaAs, SiGe, BiCMOS and bulk silicon CMOS in applications where RF performance, low power and integration are paramount.

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ADD TWO/PE42110 Multi-switch

About Peregrine Semiconductor

Peregrine Semiconductor Corporation designs, manufactures, and markets high-performance communications RF ICs for the wireless infrastructure and mobile wireless; broadband CATV/DTV; communications infrastructure; and aerospace and avionics markets. Manufactured on the Company's proprietary UltraCMOS™ mixed-signal process technology, Peregrine products are uniquely poised to meet the needs of a global RF design community in high-growth applications such as WCDMA, EDGE and GSM digital cellular, broadband, DTV, DVR and rad-hard space and defense programs. Peregrine UltraCMOS devices are manufactured in its CMOS facility located in Sydney, Australia and in Tokyo, Japan through an alliance with OKI Electric Industry Co., Ltd. The Company, headquartered in San Diego, California, maintains global sales support operations and a worldwide technical distribution network. Additional information is available on the web at psemi.com. Contact Peregrine's worldwide distribution partner, Richardson Electronics (NASDAQ: RELL), for sales information at 1-800-737-6937.

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